CMOS Analog Switches

The HI-300 thru HI-307 series of switches are monolithic devices fabricated using CMOS technology and the Intersil dielectric isolation process. These switches feature break before-make switching, (HI-301, HI-303 and HI-307 only), low and nearly constant ON resistance over the full analog signal range, and low power dissipation, (a few mW for the HI-300 thru HI-303, a few hundred mW for the HI-307).

The HI-300 thru HI-303 are TTL compatible and have a logic “0” condition with an input less than 0.8V and a logic “1” condition with an input greater than 4V. The HI-307 switches are CMOS compatible and have a low state with an input less than 3.5V and a high state with an input greater than 11V. (See pinouts for switch conditions with a logic “1” input.)

Ordering Information

PART NUMBER	TEMP. RANGE (^{o}C)	PACKAGE	PKG. NO.
HI1-0300-2	-55 to 125	14 Ld CERDIP	F14.3
HI9P0301-5	0 to 75	14 Ld SOIC	M14.15
HI1-0303-2	-55 to 125	14 Ld CERDIP	F14.3
HI1-0303-5	0 to 75	14 Ld CERDIP	F14.3
HI3-0303-5	0 to 75	14 Ld PDIP	E14.3
HI9P0303-5	0 to 75	14 Ld SOIC	M14.15
HI9P0303-9	-40 to 85	14 Ld SOIC	M14.15
HI1-0307-5	0 to 75	14 Ld CERDIP	F14.3

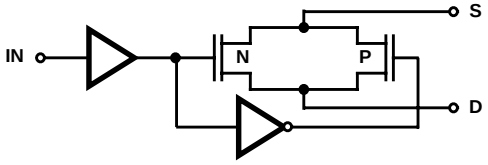
Features

- Analog Signal Range (±15V Supplies) . . . . . ±15V
- Low Leakage at 25^{o}C 40pA
- Low Leakage at 125^{o}C 1nA
- Low On Resistance at 25^{o}C 35Ω
- Break-Before-Make Delay 60ns
- Charge Injection 30pC
- TTL, CMOS Compatible
- Symmetrical Switch Elements
- Low Operating Power (Typ for HI-300 thru HI-303) . . 1.0mW

Applications

- Sample and Hold (i.e., Low Leakage Switching)
- Op Amp Gain Switching (i.e., Low On Resistance)
- Portable, Battery Operated Circuits
- Low Level Switching Circuits
- Dual or Single Supply Systems

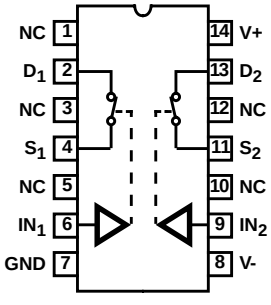
Functional Diagram



Pinouts

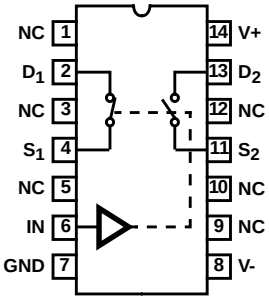
Switch States Shown For A Logic “1” Input

DUAL SPST HI-300 (CERDIP)
TOP VIEW



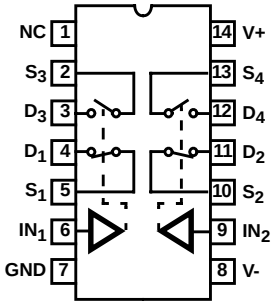
LOGIC	SWITCHES
0	OFF
1	ON

SPST HI-301 (SOIC)
TOP VIEW



LOGIC	SW1	SW2
0	OFF	ON
1	ON	OFF

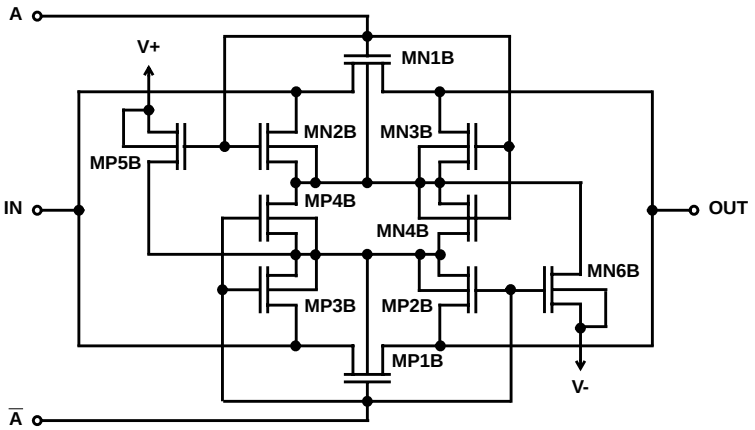
DUAL SPDT HI-303 (PDIP, CERDIP, SOIC) HI-307 (CERDIP)
TOP VIEW



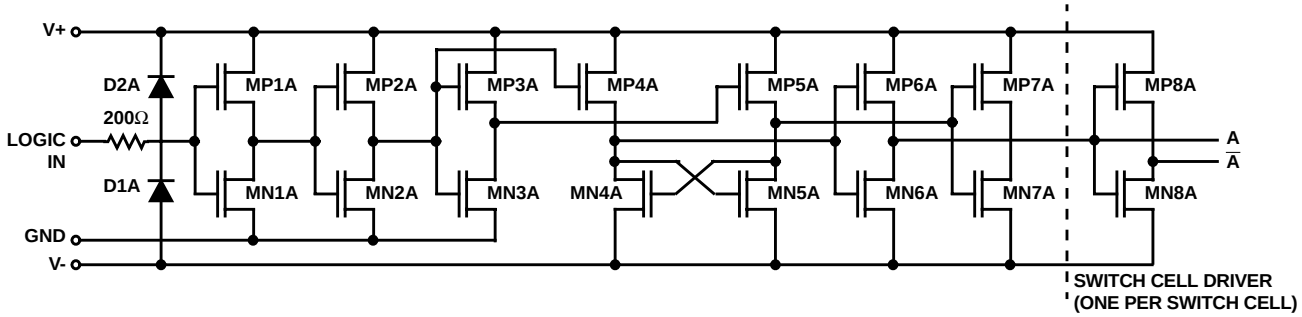
LOGIC	SW1 SW2	SW3 SW4
0	OFF	ON
1	ON	OFF

Schematic Diagrams

SWITCH CELL



DIGITAL INPUT BUFFER AND LEVEL SHIFTER



Absolute Maximum Ratings

Voltage Between Supplies (V+ to V-) . . . . . 44V (±22V)
Digital Input Voltage . . . . . (V+) +4V to (V-) -4V
Analog Input Voltage . . . . . (V+) +1.5V to (V-) -1.5V
Typical Derating Factor . . . . . 1.5mA/MHz Increase in ICCOP
ESD Classification . . . . . Class 1

Operating Conditions

Temperature Range
HI-3XX-2. . . . . -55°C to 125°C
HI-3XX-5. . . . . 0°C to 75°C
HI-3XX-9. . . . . -40°C to 85°C

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (°C/W)	θ_{JC} (°C/W)
CERDIP Package	95	40
PDIP Package	100	N/A
SOIC Package	120	N/A

Maximum Junction Temperature
Ceramic Packages . . . . . 175°C
Plastic Packages . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications

Supplies = +15V, -15V; V_{IN} = Logic Input. HI-300 thru HI-303: V_{IN} - for Logic "1" = 4V, for Logic "0" = 0.8V. HI-307: V_{IN} - for Logic "1" = 11V, for Logic "0" = 3.5V, Unless Otherwise Specified

PARAMETER	TEMP (°C)	-2			-5, -9			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
DYNAMIC CHARACTERISTICS								
Switch ON Time, t_{ON} (Note 13)	25	-	210	300	-	210	300	ns
Switch OFF Time, t_{OFF} (Note 13)	25	-	160	250	-	160	250	ns
Switch ON Time, t_{ON} (Note 14)	25	-	160	250	-	160	250	ns
Switch OFF Time, t_{OFF} (Note 14)	25	-	100	150	-	100	150	ns
Break-Before-Make Delay, t_{OPEN} (Note 15)	25	-	60	-	-	60	-	ns
Charge Injection Voltage, ΔV (Note 7)	25	-	3	-	-	3	-	mV
OFF Isolation (Note 6)	25	-	60	-	-	60	-	dB
Input Switch Capacitance, $C_{S(OFF)}$	25	-	16	-	-	16	-	pF
Output Switch Capacitance, $C_{D(OFF)}$	25	-	14	-	-	14	-	pF
Output Switch Capacitance, $C_{D(ON)}$	25	-	35	-	-	35	-	pF
Digital Input Capacitance, C_{IN}	25	-	5	-	-	5	-	pF
DIGITAL INPUT CHARACTERISTICS								
Input Low Level, V_{INL} (Note 13)	Full	-	-	0.8	-	-	0.8	V
Input High Level, V_{INH} (Note 13)	Full	4	-	-	4	-	-	V
Input Low Level, V_{INL} (Note 14)	Full	-	-	3.5	-	-	3.5	V
Input High Level, V_{INH} (Note 14)	Full	11	-	-	11	-	-	V
Input Leakage Current (Low), I_{INL} (Note 5)	Full	-	-	1	-	-	1	µA
Input Leakage Current (High), I_{INH} (Note 5)	Full	-	-	1	-	-	1	µA
ANALOG SWITCH CHARACTERISTICS								
Analog Signal Range	Full	-15	-	+15	-15	-	+15	V
ON Resistance, r_{ON} (Note 2)	25	-	35	50	-	35	50	Ω
	Full	-	40	75	-	40	75	Ω
OFF Input Leakage Current, $I_{S(OFF)}$ (Note 3)	25	-	0.04	1	-	0.04	5	nA
	Full	-	1	100	-	0.2	100	nA
OFF Output Leakage Current, $I_{D(OFF)}$ (Note 3)	25	-	0.04	1	-	0.04	5	nA
	Full	-	1	100	-	0.2	100	nA
ON Leakage Current, $I_{D(ON)}$ (Note 4)	25	-	0.03	1	-	0.03	5	nA
	Full	-	0.5	100	-	0.2	100	nA
POWER SUPPLY CHARACTERISTICS								
Current, I+ (Notes 8, 13)	25	-	0.09	0.5	-	0.09	0.5	mA
	Full	-	-	1	-	-	1	mA

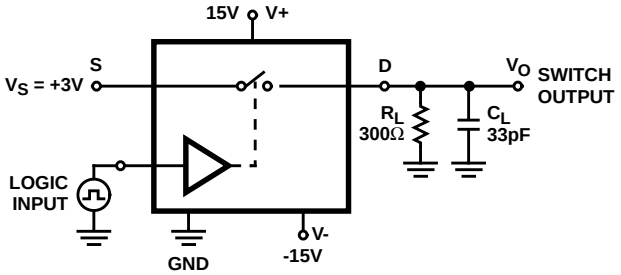
Electrical Specifications Supplies = +15V, -15V; V_{IN} = Logic Input. HI-300 thru HI-303: V_{IN} - for Logic "1" = 4V, for Logic "0" = 0.8V. HI-307: V_{IN} - for Logic "1" = 11V, for Logic "0" = 3.5V, Unless Otherwise Specified **(Continued)**

PARAMETER	TEMP (^oC)	-2			-5, -9			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Current, I- (Notes 8, 13)	25	-	0.01	10	-	0.01	100	µA
	Full	-	-	100	-	-	-	µA
Current, I+ (Notes 9, 13)	25	-	0.01	10	-	0.01	100	µA
	Full	-	-	100	-	-	-	µA
Current, I- (Notes 9, 13)	25	-	0.01	10	-	0.01	100	µA
	Full	-	-	100	-	-	-	µA
Current, I+ (Notes 10, 14)	25	-	0.01	10	-	0.01	100	µA
	Full	-	-	100	-	-	-	µA
Current, I- (Notes 10, 14)	25	-	0.01	10	-	0.01	100	µA
	Full	-	-	100	-	-	-	µA
Current, I+ (Notes 11, 14)	25	-	0.01	10	-	0.01	100	µA
	Full	-	-	100	-	-	-	µA
Current, I- (Notes 11, 14)	25	-	0.01	10	-	0.01	100	µA
	Full	-	-	100	-	-	-	µA

NOTES:

2. $V_S = \pm 10V$, $I_{OUT} = \mp 10mA$. On resistance derived from the voltage measured across the switch under these conditions.
3. $V_S = \pm 14V$, $V_D = \mp 14V$.
4. $V_S = V_D = \pm 14V$.
5. The digital inputs are diode protected MOS gates and typical leakages of 1nA or less can be expected.
6. $V_S = 1V_{RMS}$, f = 500kHz, C_L = 15pF, R_L = 1K.
7. V_S = 0V, C_L = 10nF, Logic Drive = 5V pulse (HI-300 - 303), 15V pulse (HI-307). Switches are symmetrical; S and D may be interchanged. Charge Injection = Q = C_L x ΔV.
8. V_{IN} = 4V (one input, all other inputs = 0V).
9. V_{IN} = 0.8V (all inputs).
10. V_{IN} = 15V (all inputs).
11. V_{IN} = 0V (all inputs).
12. To drive from DTL/TTL circuits, pullup resistors to +5V supply are recommended.
13. HI-300 thru HI-303 only.
14. HI-307 only.
15. HI-301, HI-303, HI-307 only.

Test Circuits and Waveforms



SWITCH TYPE	V_{INH}
HI-300 thru HI-303	4V
HI-307	15V

FIGURE 1A. TEST CIRCUIT

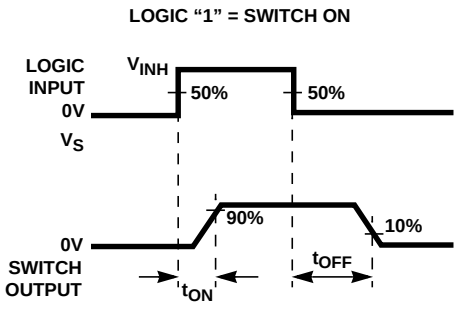


FIGURE 1B. MEASUREMENT POINTS

FIGURE 1. SWITCH t_{ON} AND t_{OFF}

Test Circuits and Waveforms (Continued)

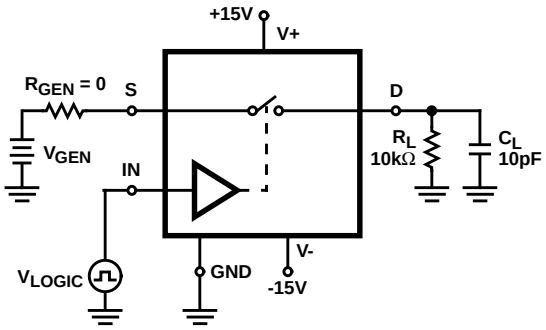


FIGURE 2A. TEST CIRCUIT

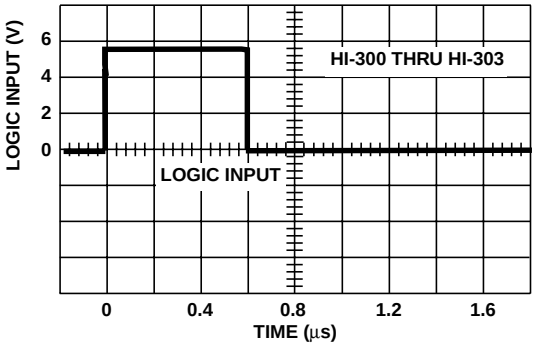


FIGURE 2B. TTL LOGIC INPUT

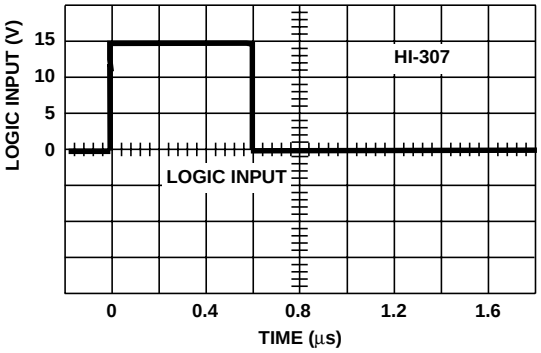


FIGURE 2C. CMOS LOGIC INPUT

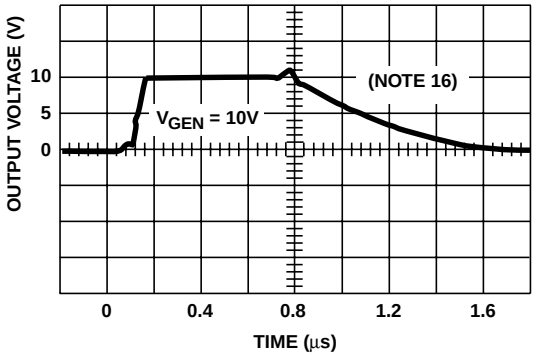


FIGURE 2D. V_{ANALOG} = 10V

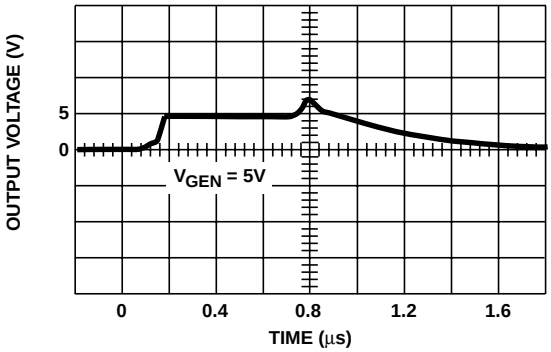


FIGURE 2E. V_{ANALOG} = 5V

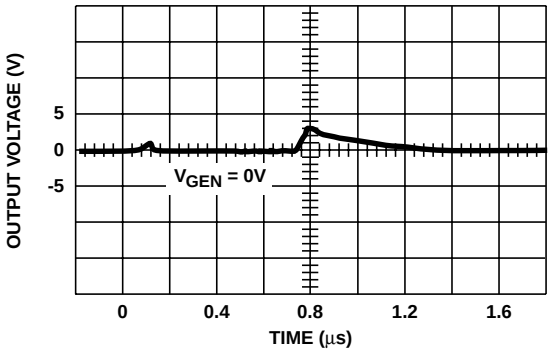


FIGURE 2F. V_{ANALOG} = 0V

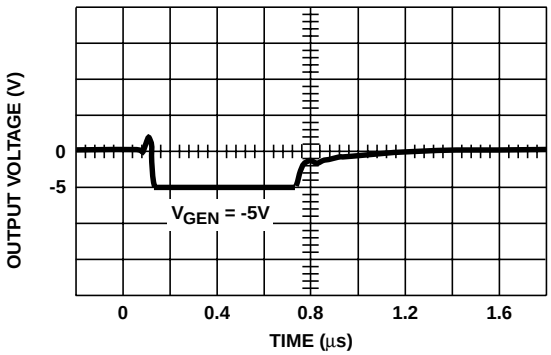


FIGURE 2G. V_{ANALOG} = -5V

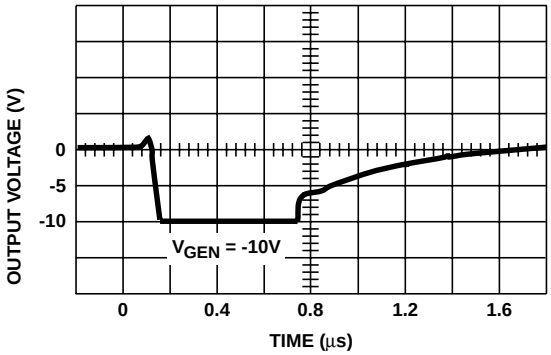


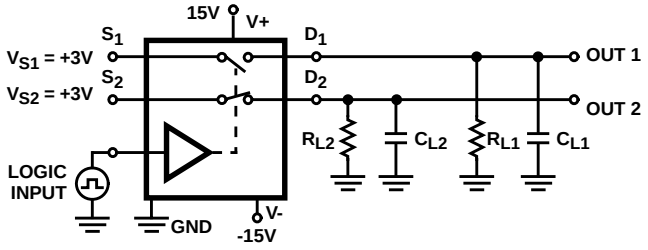
FIGURE 2H. V_{ANALOG} = -10V

NOTE:

16. If R_{GEN}, R_L or C_L is increased, there will be proportional increases in rise and/or fall RC times.

FIGURE 2. SWITCHING WAVEFORMS FOR VARIOUS ANALOG INPUT VOLTAGES

Test Circuits and Waveforms (Continued)



SWITCH TYPE	V_{INH}
HI-301, HI-303	5V
HI-307	15V

FIGURE 3A. TEST CIRCUIT

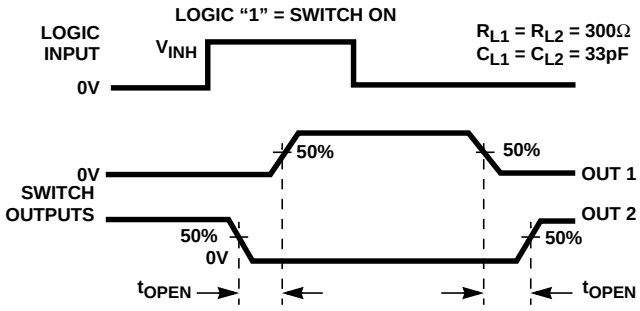


FIGURE 3B. MEASUREMENT POINTS

FIGURE 3. BREAK-BEFORE-MAKE DELAY (t_{OPEN})

Typical Performance Curves

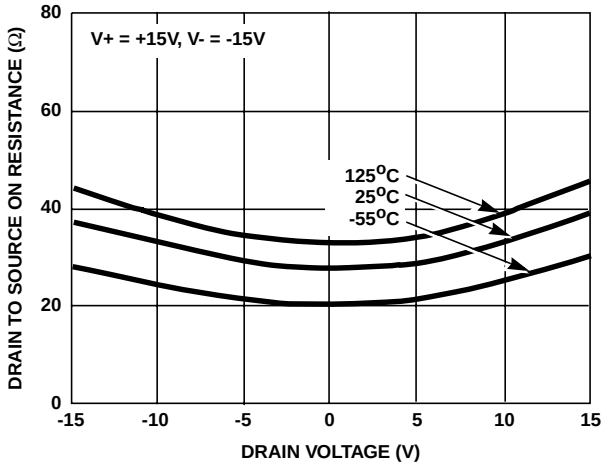


FIGURE 4. $r_{DS(ON)}$ vs V_D

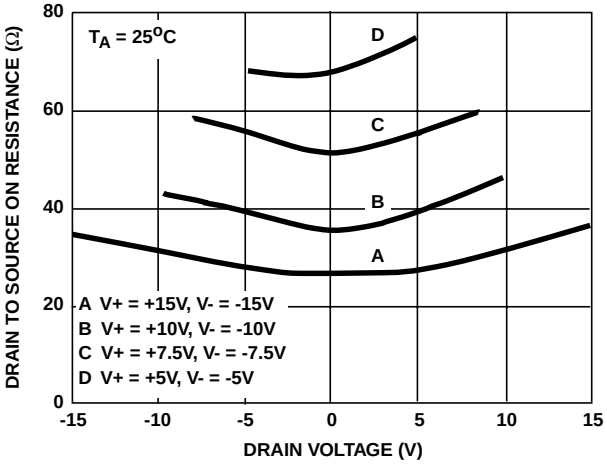


FIGURE 5. $r_{DS(ON)}$ vs V_D

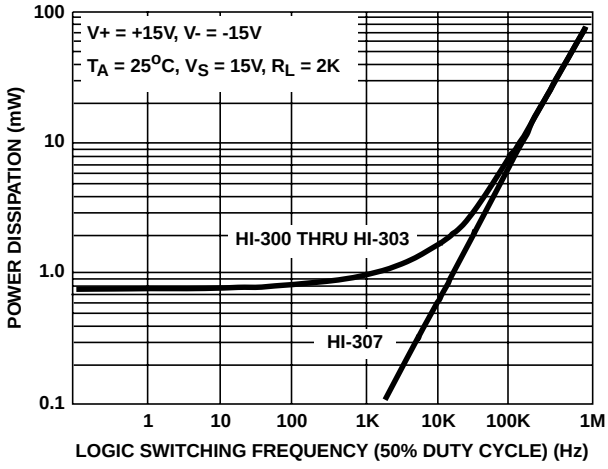


FIGURE 6. DEVICE POWER DISSIPATION vs SWITCHING FREQUENCY (SINGLE LOGIC INPUT)

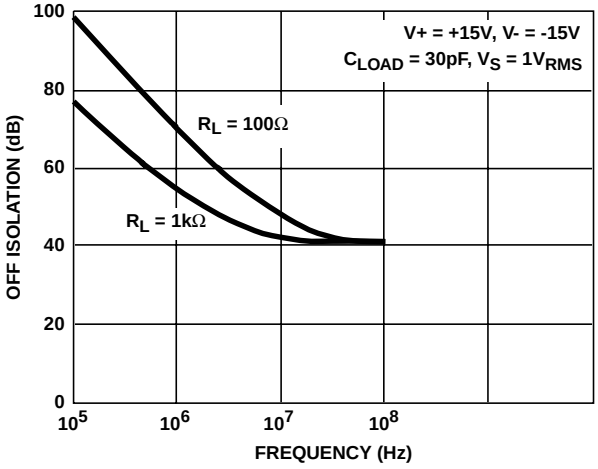


FIGURE 7. OFF ISOLATION vs FREQUENCY

Typical Performance Curves (Continued)

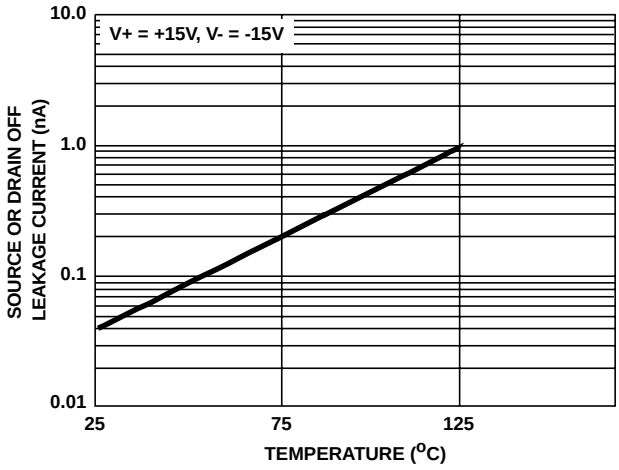


FIGURE 8. $I_{S(OFF)}$ OR $I_{D(OFF)}$ vs TEMPERATURE†

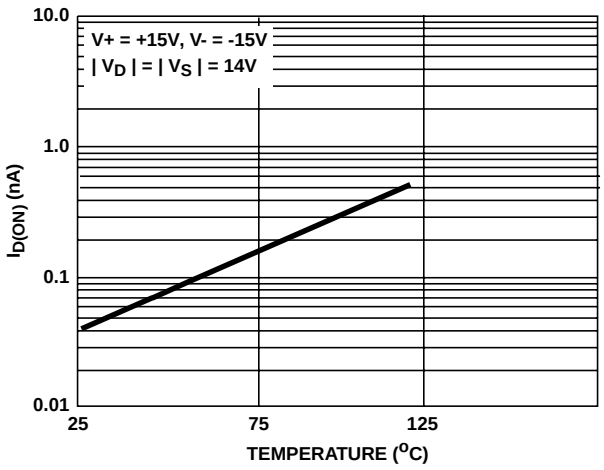


FIGURE 9. $I_{D(ON)}$ vs TEMPERATURE†

† The net leakage into the source or drain is the N-Channel leakage minus the P-Channel leakage. This difference can be positive, negative or zero depending on the analog voltage and temperature, and will vary greatly from unit to unit.

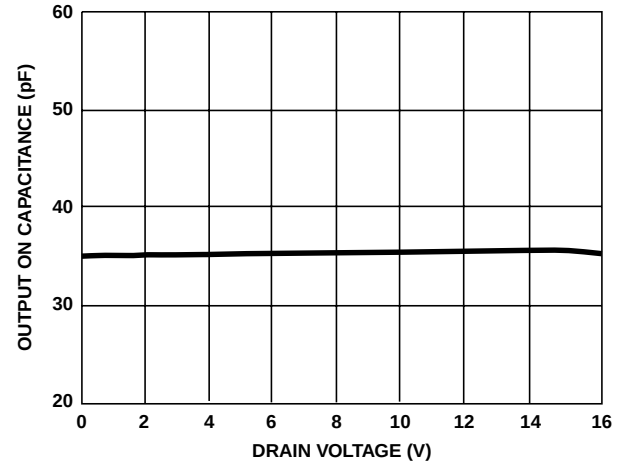


FIGURE 10. OUTPUT ON CAPACITANCE vs DRAIN VOLTAGE

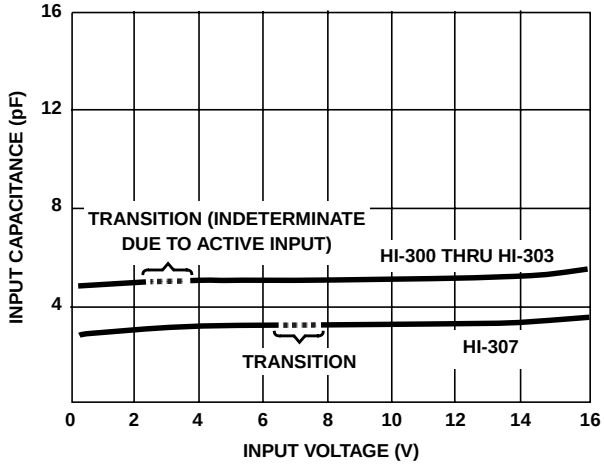


FIGURE 11. DIGITAL INPUT CAPACITANCE vs INPUT VOLTAGE

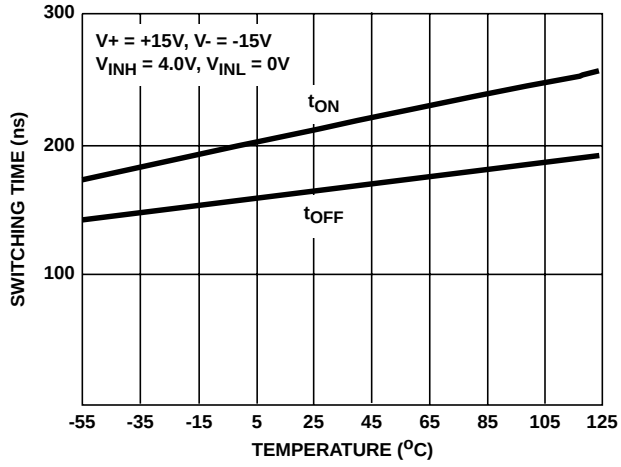


FIGURE 12. SWITCHING TIME vs TEMPERATURE, HI-300 THRU HI-303

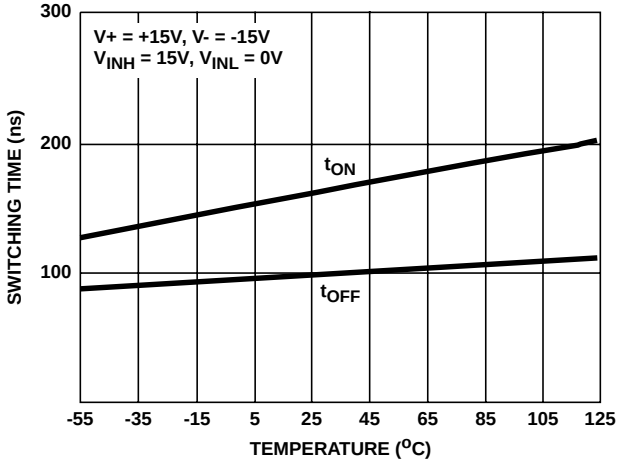


FIGURE 13. SWITCHING TIME vs TEMPERATURE, HI-307

Typical Performance Curves (Continued)

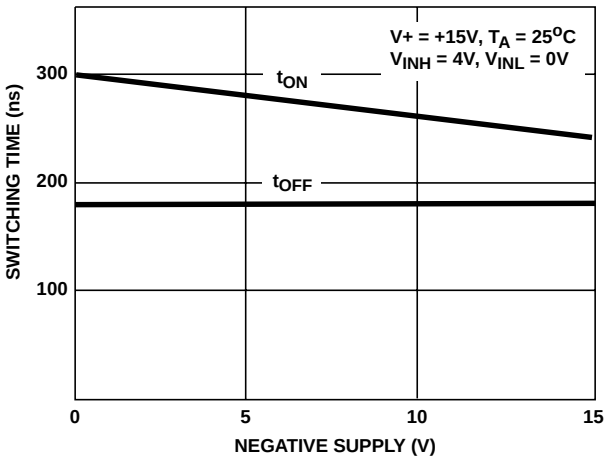


FIGURE 14. SWITCHING TIME vs NEGATIVE SUPPLY VOLTAGE, HI-300 THRU HI-303

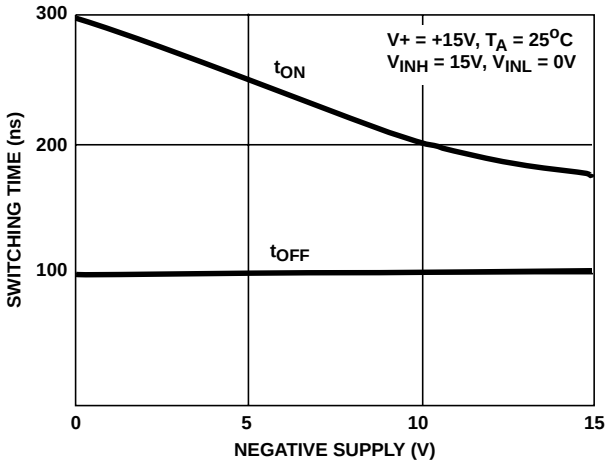


FIGURE 15. SWITCHING TIME vs NEGATIVE SUPPLY VOLTAGE, HI-307

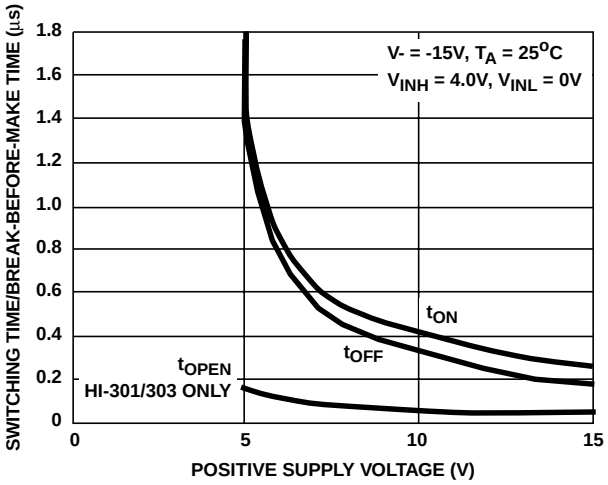


FIGURE 16. SWITCHING TIME AND BREAK-BEFORE-MAKE TIME vs POSITIVE SUPPLY VOLTAGE, HI-300 THRU HI-303

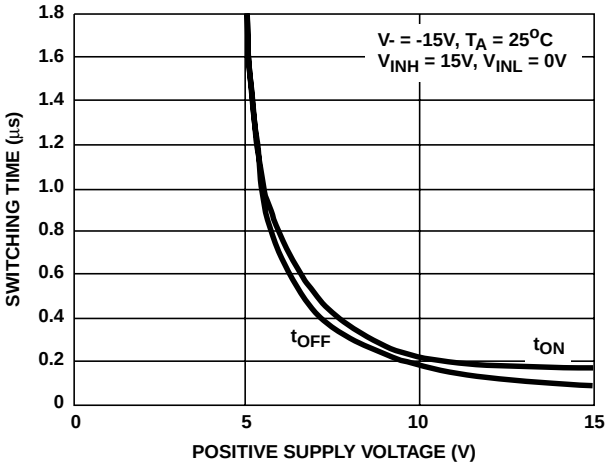


FIGURE 17. SWITCHING TIME vs POSITIVE SUPPLY VOLTAGE, HI-307

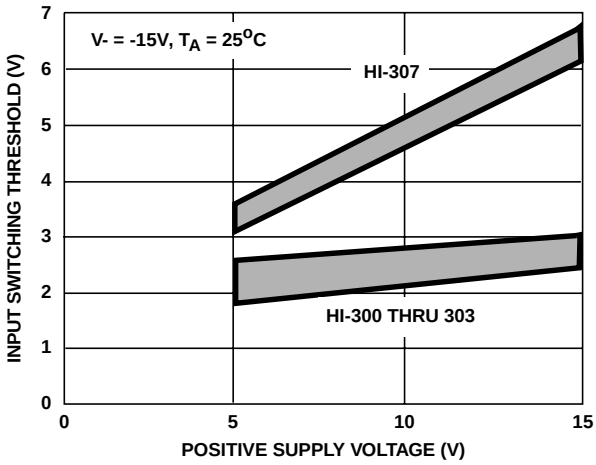


FIGURE 18. INPUT SWITCHING THRESHOLD vs POSITIVE SUPPLY VOLTAGE